



### 30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

-70 A

#### **Features**

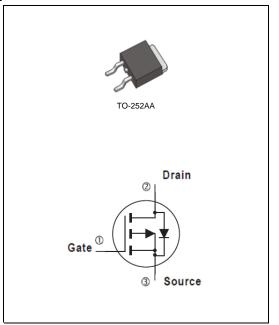
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-10V,I<sub>D</sub>@-10A<8.5mΩ
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-4.5V,I<sub>D</sub>@-8A<14mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std.. (Halogen Free)



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER  Drain-Source Voltage  Gate-Source Voltage		SYMBOL	LIMIT	UNITS	
		V <sub>DS</sub>	-30 <u>+</u> 20	V	
				V	
Continuous Drain Current	T <sub>C</sub> =25°C	I <sub>D</sub>	-70		
	T <sub>C</sub> =100°C		-44	А	
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	-280		
Power Dissipation	T <sub>C</sub> =25°C	Po	63		
	T <sub>C</sub> =100°C		25	W	
Continuous Drain Current	T <sub>A</sub> =25°C	I <sub>D</sub>	-11	А	
	T <sub>A</sub> =70°C		-8.8	А	
Power Dissipation	T <sub>A</sub> =25°C	_	2.0	10/	
Power Dissipation	T <sub>A</sub> =70°C	Po	1.3	W	
Operating Junction and Storage Temperature Range		$T_{J}$ , $T_{STG}$	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5)</sup>	Junction to Case	$R_{ heta JC}$	2.0	0000	
	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W	

• Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-1.0	-1.5	-2.5	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-10A	-	7.1	8.5	mΩ	
		V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-8A	-	10	14		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1.0	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	$Q_{g}$	V <sub>DS</sub> =-15V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	27	-	nC	
Gate-Source Charge	$Q_gs$		-	8.4	-		
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =-4.5 V	-	8.7	-		
Input Capacitance	Ciss	\/ 45\/ \/ 0\/	-	3228	-	pF	
Output Capacitance	Coss	$V_{DS}$ =-15V, $V_{GS}$ =0V, f=1.0MHZ	-	396	-		
Reverse Transfer Capacitance	Crss	I=1.0IVII IZ	-	254	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/\D 44	-	10	-		
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =-15V,ID=-1A, $V_{GS}$ =-10V, $R_{G}$ =6 $\Omega$	-	13	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	(Note 1,2)	-	111	-		
Turn-Off Fall Time	t <sub>f</sub>		-	51	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı		-	-	-70	А	
Diode Forward Current	I <sub>S</sub>						
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A,V <sub>GS</sub> =0V	-	-0.7	-1.0	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 4. The maximum current rating is package limited
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper
- 6. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

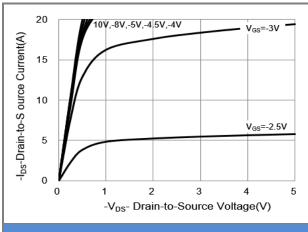
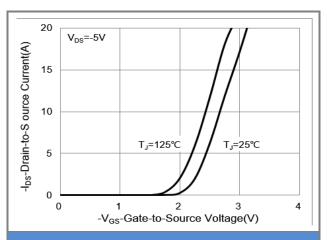


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

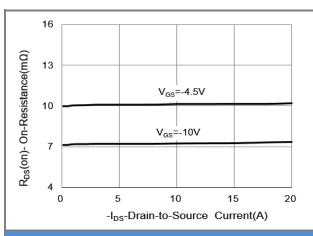


Fig.3 On-Resistance vs. Drain Current

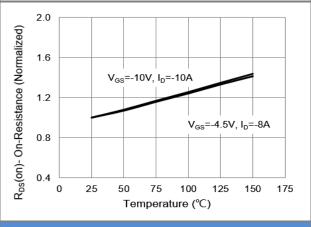


Fig.4 On-Resistance vs. Junction temperature

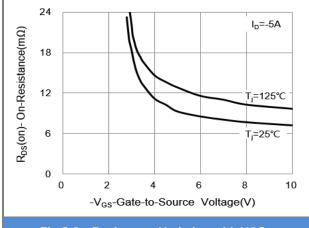
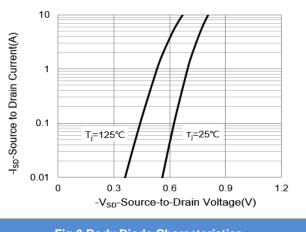


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 





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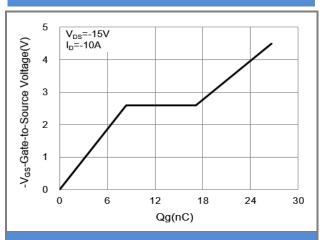


Fig.7 Gate-Charge Characteristics

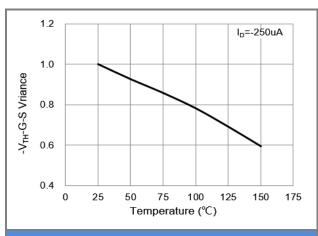
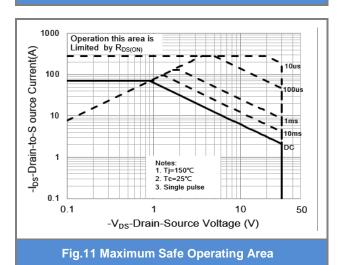


Fig.9 Threshold Voltage Variation with Temperature.



1.2 I<sub>D</sub>=-250uA BVDSS- Drain-to-Source Voltage(V) 1.1 1.0 0.9 8.0 0 25 125 150 175 50 75 100 Temperature (°C)

Fig.8 Breakdown Voltage Variation vs. Temperature

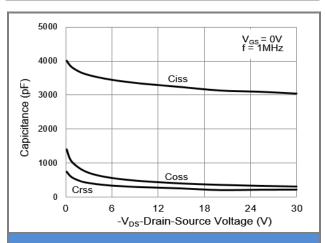
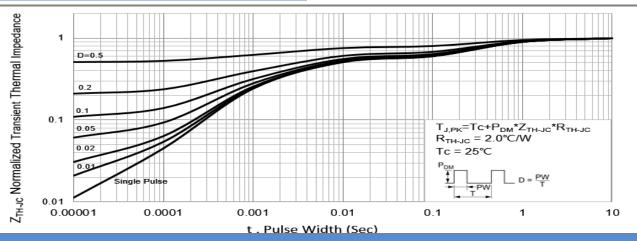


Fig.10 Capacitance vs. Drain-Source Voltage.





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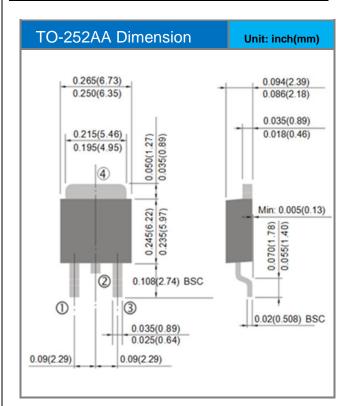


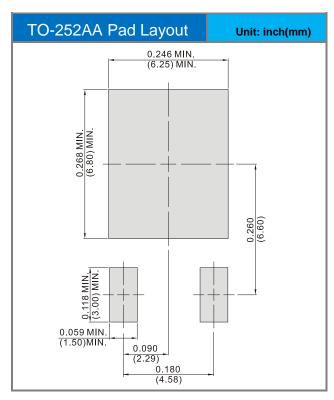
**Fig.12 Normalized Thermal Transient Impedance** 





#### **Packaging Information**









### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD70P03_L2_00001	TO-252AA	3,000pcs / 13" reel	D70P03	Halogen free





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